

19th RD50 Workshop (CERN)

Monday, 21 November 2011

Defect/Material characterisation - 503/1-001 - Council Chamber (13:30 - 17:00)

-Conveners: Mara Bruzzi

time	[id] title	presenter
13:30	[33] Welcome	CASSE, Gianluigi MOLL, Michael
13:40	[14] Effect of oxygen on annealing induced defects transformations in epitaxial silicon irradiated with high energy protons	KAMINSKI, Pawel
14:00	[15] A comparative study of mixed irradiated sensors made of different silicon base material	EBER, Robert
14:20	[16] Depletion Voltage and Effective Doping Concentration of Float Zone and Magnetic Czochralski Silicon Diodes Irradiated by Protons to Conditions Relevant to the High Luminosity LHC	SEIDEL, Sally
14:40	[23] Nitrogen-doped silicon as a potentially radiation-hard material	KAMINSKI, Pawel
15:00	Coffee break	
15:30	[29] The peculiarities of photoconductivity in the irradiated Si.	Prof. VAITKUS, Juozas
15:50	[27] Signals of heavily irradiated Si particle detectors	Prof. VAITKUS, Juozas
16:10	[75] Discussion	